

POWER MOS 7™

Power MOS 7™ is a new generation of low loss, high voltage, N-Channel enhancement mode power MOSFETs. Both conduction and switching losses are addressed with Power MOS 7™ by significantly lowering $R_{DS(ON)}$ and Q_g . Power MOS 7™ combines lower conduction and switching losses along with exceptionally fast switching speeds inherent with APT's patented metal gate structure.

- Lower Input Capacitance
- Increased Power Dissipation
- Lower Miller Capacitance
- Easier To Drive
- Lower Gate Charge, Q_g
- Popular SOT-227 Package

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

| Symbol | Parameter | APT50M65JLL | UNIT |
|----------------|---|-------------|---------------------|
| V_{DSS} | Drain-Source Voltage | 500 | Volts |
| I_D | Continuous Drain Current @ $T_C = 25^\circ\text{C}$ | 60 | Amps |
| I_{DM} | Pulsed Drain Current ① | 240 | |
| V_{GS} | Gate-Source Voltage Continuous | ± 30 | Volts |
| V_{GSM} | Gate-Source Voltage Transient | ± 40 | |
| P_D | Total Power Dissipation @ $T_C = 25^\circ\text{C}$ | 540 | Watts |
| | Linear Derating Factor | 4.32 | W/ $^\circ\text{C}$ |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to 150 | $^\circ\text{C}$ |
| T_L | Lead Temperature: 0.063" from Case for 10 Sec. | 300 | |
| I_{AR} | Avalanche Current ① (Repetitive and Non-Repetitive) | 60 | Amps |
| E_{AR} | Repetitive Avalanche Energy ① | 50 | |
| E_{AS} | Single Pulse Avalanche Energy ④ | 3000 | mJ |

STATIC ELECTRICAL CHARACTERISTICS

| Symbol | Characteristic / Test Conditions | MIN | TYP | MAX | UNIT |
|--------------|---|-----|-----|-----------|---------------|
| BV_{DSS} | Drain-Source Breakdown Voltage ($V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$) | 500 | | | Volts |
| $I_{D(on)}$ | On State Drain Current ② ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10\text{V}$) | 60 | | | Amps |
| $R_{DS(on)}$ | Drain-Source On-State Resistance ② ($V_{GS} = 10\text{V}$, $0.5 I_{D[Cont.]}$) | | | 0.065 | Ohms |
| I_{DSS} | Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}$, $V_{GS} = 0\text{V}$) | | | 25 | μA |
| | Zero Gate Voltage Drain Current ($V_{DS} = 0.8 V_{DSS}$, $V_{GS} = 0\text{V}$, $T_C = 125^\circ\text{C}$) | | | 250 | |
| I_{GSS} | Gate-Source Leakage Current ($V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$) | | | ± 100 | nA |
| $V_{GS(th)}$ | Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 2.5\text{mA}$) | 3 | | 5 | Volts |

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

APT50M65JLL

| Symbol | Characteristic | Test Conditions | MIN | TYP | MAX | UNIT |
|--------------|------------------------------|---|-----|------|-----|------|
| C_{iss} | Input Capacitance | $V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$ | | 6940 | | pF |
| C_{oss} | Output Capacitance | | | 1430 | | |
| C_{rss} | Reverse Transfer Capacitance | | | 108 | | |
| Q_g | Total Gate Charge ③ | $V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_{D[\text{Cont.}]} @ 25^\circ\text{C}$ | | 174 | | nC |
| Q_{gs} | Gate-Source Charge | | | 45 | | |
| Q_{gd} | Gate-Drain ("Miller") Charge | | | 79 | | |
| $t_{d(on)}$ | Turn-on Delay Time | $V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_{D[\text{Cont.}]} @ 25^\circ\text{C}$ $R_G = 0.6\Omega$ | | 19 | | ns |
| t_r | Rise Time | | | 15 | | |
| $t_{d(off)}$ | Turn-off Delay Time | | | 43 | | |
| t_f | Fall Time | | | 6 | | |

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

| Symbol | Characteristic / Test Conditions | MIN | TYP | MAX | UNIT |
|----------|---|-----|------|-----|---------------|
| I_S | Continuous Source Current (Body Diode) | | | 60 | Amps |
| I_{SM} | Pulsed Source Current ① (Body Diode) | | | 240 | |
| V_{SD} | Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -I_{D[\text{Cont.}]}^*$) | | | 1.3 | Volts |
| t_{rr} | Reverse Recovery Time ($I_S = -I_{D[\text{Cont.}]}^*$, $dI_S/dt = 100A/\mu\text{s}$) | | 680 | | ns |
| Q_{rr} | Reverse Recovery Charge ($I_S = -I_{D[\text{Cont.}]}^*$, $dI_S/dt = 100A/\mu\text{s}$) | | 17.0 | | μC |

THERMAL CHARACTERISTICS

| Symbol | Characteristic | MIN | TYP | MAX | UNIT |
|-----------------|---------------------|-----|-----|------|---------------------------|
| $R_{\theta JC}$ | Junction to Case | | | 0.23 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Junction to Ambient | | | 40 | |

① Repetitive Rating: Pulse width limited by maximum junction temperature.

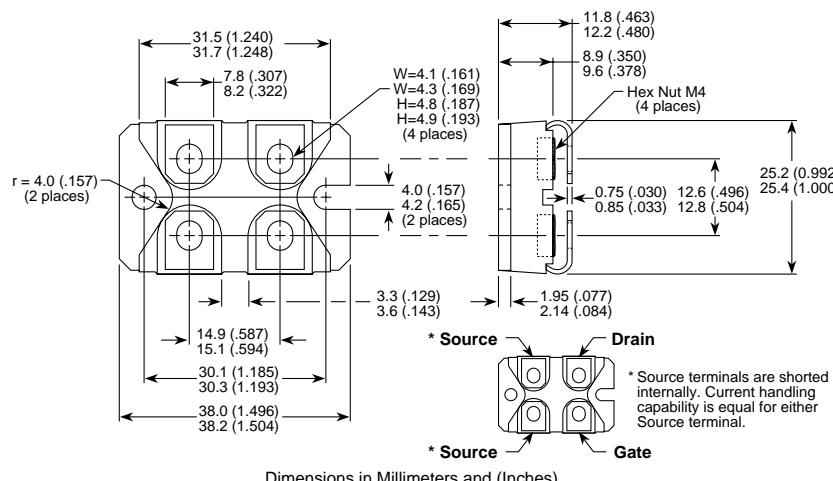
③ See MIL-STD-750 Method 3471

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

④ Starting $T_j = +25^\circ\text{C}$, $L = 1.67\text{mH}$, $R_G = 25\Omega$, Peak $I_L = 60\text{A}$

APT Reserves the right to change, without notice, the specifications and information contained herein.

SOT-227 (ISOTOP®) Package Outline



APT's devices are covered by one or more of the following U.S. patents: 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058